

Next Generation of Terahertz Sources and Detectors

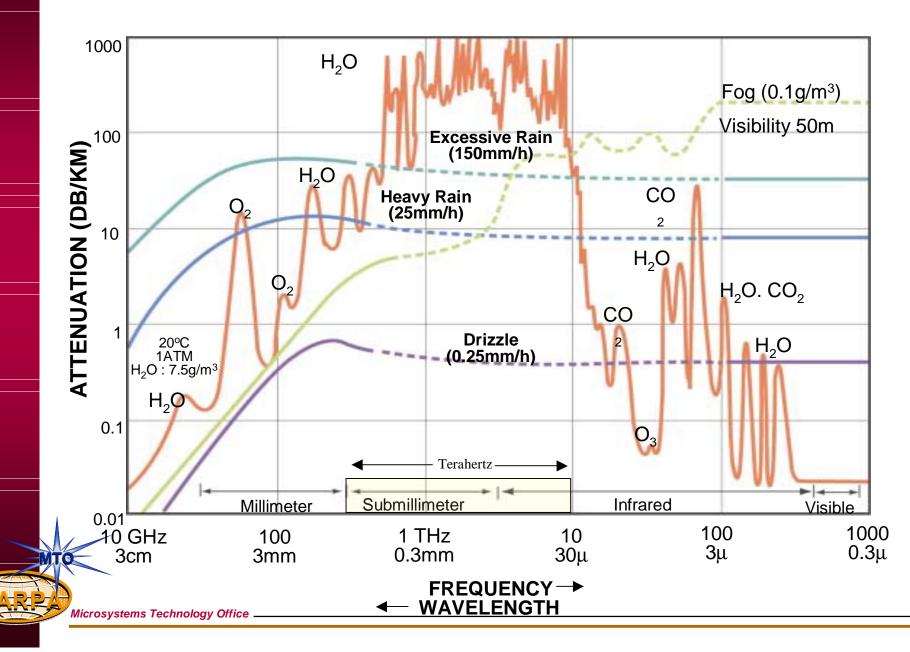
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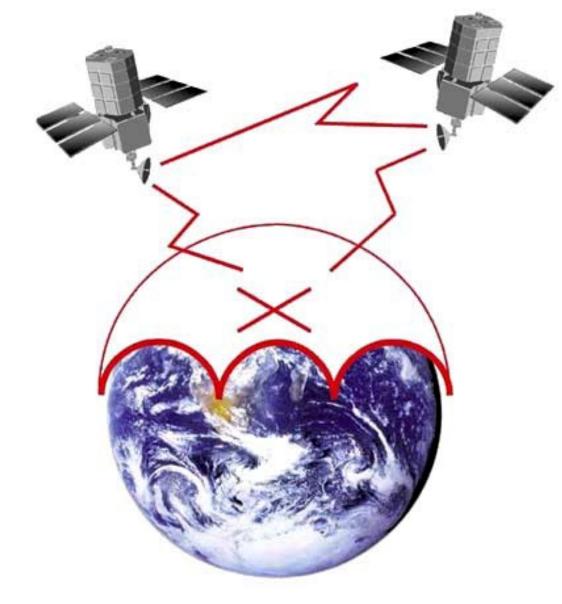
E/M Attenuation vs Frequency Limitations of Current Technology





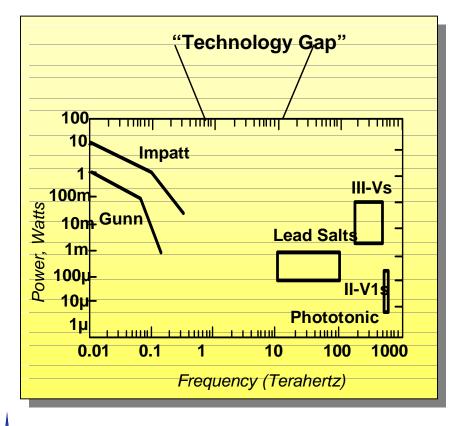
Using a limitation to our advantage!!!







Program Objectives



Explore innovative semiconductor device and circuit concepts for the demonstration of high power sources and high sensitivity detectors for the region of the electromagnetic spectrum between 0.3-10 THz (1 - 0.03 mm)



Technical Challenges

<u>THz Sources</u>

Achievement of high output power (at least mWs)Efficiency

Compactness

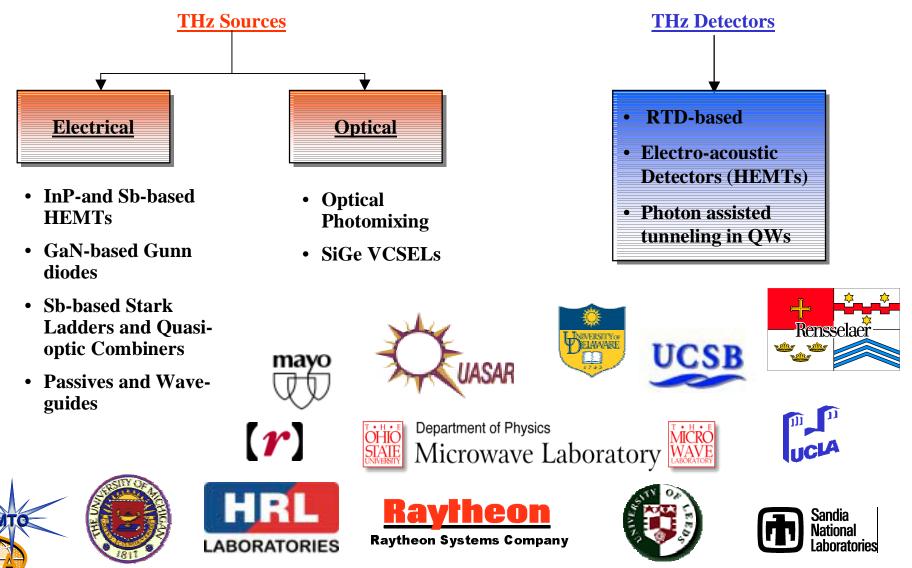
>Tunnability for certain applications

THz Detectors

High Sensitivity and Detectivity
Quantum Efficiency
Compactness



Technical Approaches



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Quantum Device Technologies for THz Communications and Imaging



OBJECTIVE:

Develop monolithic integrated circuits capable to generate power at 0.33 THz, 0.66 THz, 1 THz and 3 THz.

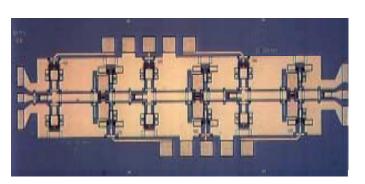
APPLICATIONS:

Remote sensingHigh resolution imagingHigh data-rate space communication

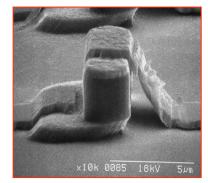
APPROACH:

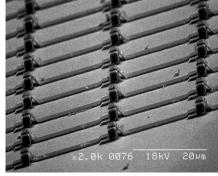
• Develop high performance HEMT MMIC sources with integrated antennas for 0.3 THz to 1 THz frequency range

• Develop novel superlattice oscillators and multipliers for 1 THz to 10 THz frequency range



State of the art HEMT MMIC



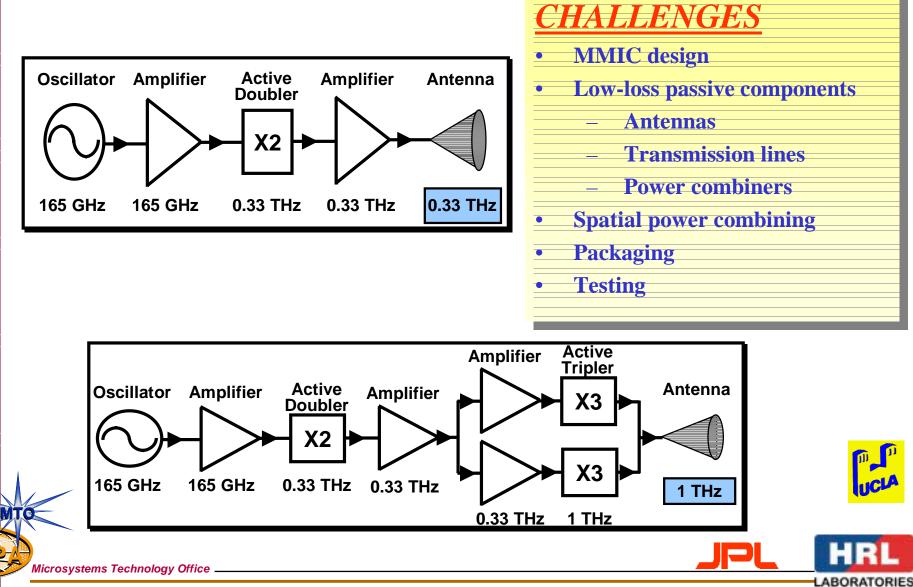


Quasi-optical superlattice array for harmonic generation









InAs/AlSb/GaSb Materials Effort



• 1-10 THz source development

- collaboration with UCSB (Allen)
- InAs/AlSb superlattice devices
- emphasis on harmonic generation

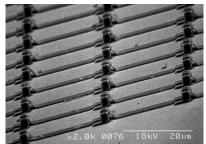
• Materials support for Raytheon (Frazier)

- RTD structures

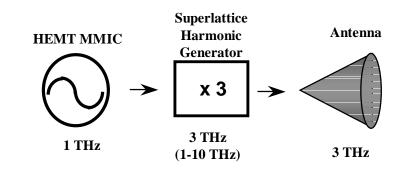
- High Jp

- IMSC MBE Capability





Quasi-optical superlattice array for harmonic generation







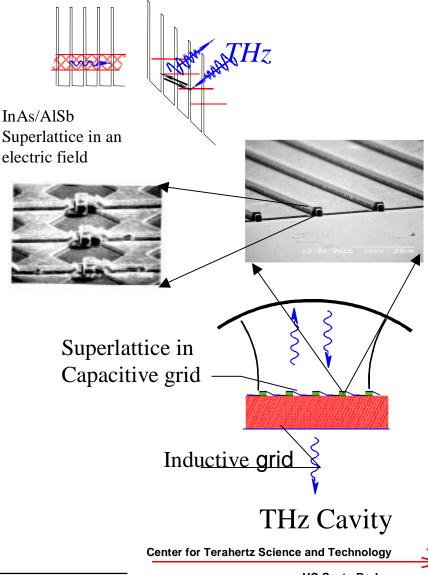
Solid State Terahertz Sources for Sensing and Satellite Communications

OBJECTIVE:

Develop and demonstrate an electrically excited solid-state Terahertz sources, capable of delivering >1 mW of power in the range above 1 THz

APPROACH:

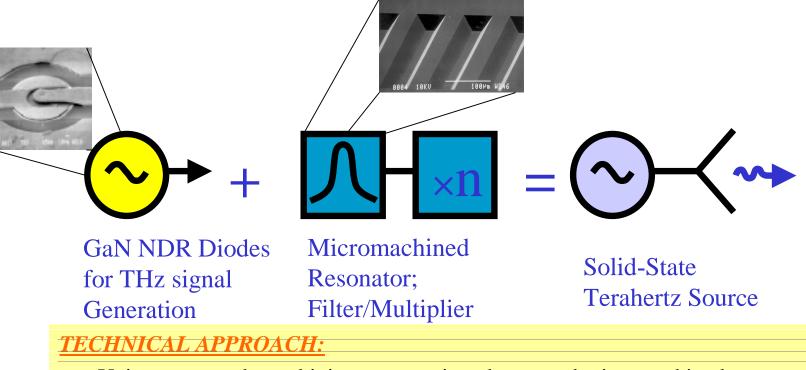
Implementation of InAs/AlSb superlattice, Stark ladders for THz generation
Implementation of Quasi-optic arrays for power combining
Demonstration of THz harmonic generation



UC Santa Barbara // http://www.qi.ucsb.edu/

Solid-State Terahertz Sources



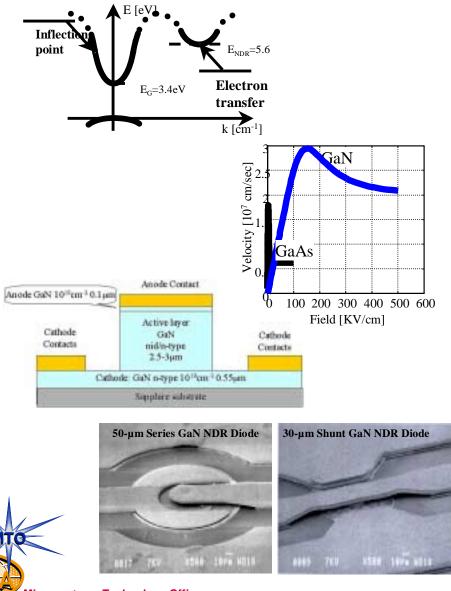


- Unique approach combining new semiconductor and micromachined concepts
- Semiconductor device potential for high-power fundamental or harmonic sources
- Possibility to apply micromachined concept to other sources developed under this program





III-N Terahertz Gunn Diodes



OBJECTIVE:

Take advantage of the electron transport and material properties of III-N semiconductors for the demonstration of Gunn diode THz sources

CHALLENGES:

- Achieve good quality GaN materials
 Demonstrate NDR performance in WBG semiconductors
- •Demonstrate generation of THz radiations



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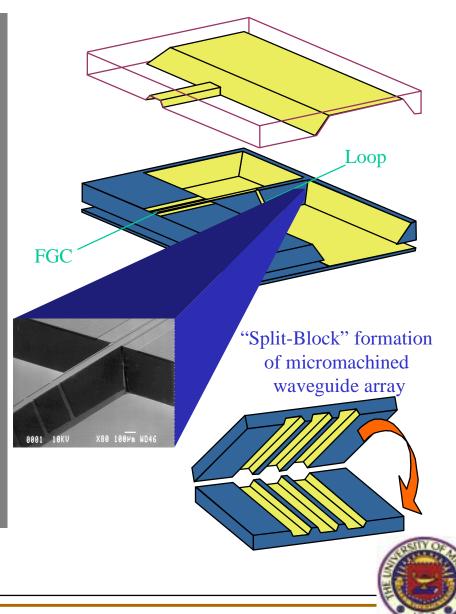
Passive Silicon Micromachined Structures for THz Applications



APPROACH:

Use Silicon Micro-machining Technology for the Development of:

- THz waveguides for high-performance low-loss circuits
- •Electric and magnetic transitions from planar transmission lines to micromachined waveguides
- Transitions between waveguides and planar micromachined antennas
- •Compact resonators for GaN Gunn sources



All-Solid-State Photomixing Transmitter



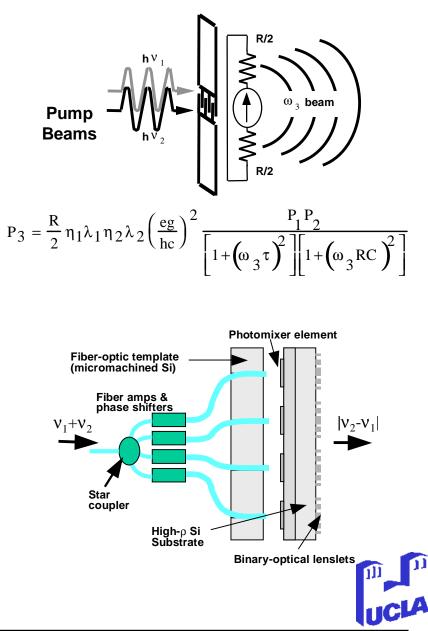
OBJECTIVES:

Develop a solid-state source for the THz region having up to 1 mW output power and:

- Stable continuous-wave performance
- Room-temperature operation
- Tunability up to ~1 octave
- Instantaneous frequency stability > 1:10⁶
- Phase lockability (required for comms)
- Good beam characteristics (TEM₀₀₀ Gaussian desirable)

TECHNICAL APPROACH:

Optical mixing in an ultrafast photoconductor (LT-GaAs)
Couple internal THz photocurrents to a THz load (antenna)
Implementation of power combining techniques



THz Sources Based on Intersubband Transitions in SiGe Quantum Wells

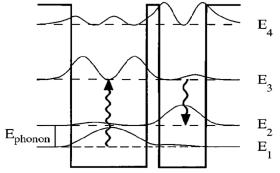


OBJECTIVE:

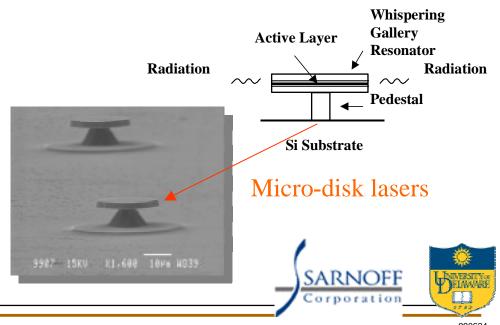
To demonstrate a SiGe, microdisk cavity, intersubband laser suitable for communication systems

APPROACH:

Silicon micromachining for novel resonator design
SiGe unipolar architecture
E/M simulation for device optimization
1-10 THz operation



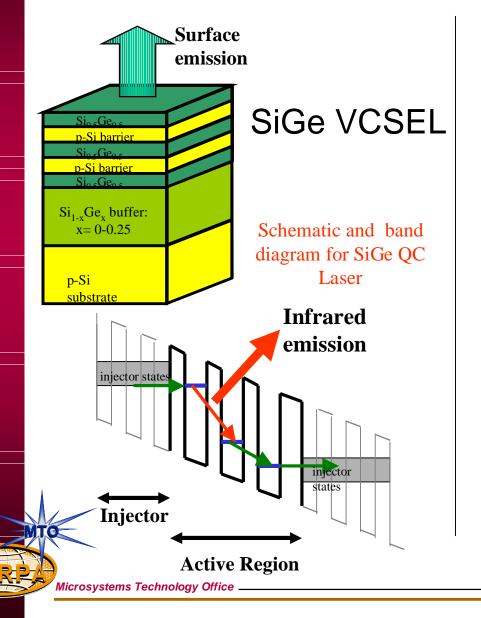
Quantum well transitions between E_3 and E_2 . Proposed device will use SiGe quantum wells and hole intersubband transitions.



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Vertical Cavity Silicon-Germanium Quantum Cascade Lasers for Terahertz Emission



OBJECTIVE:

Develop and demonstrate a vertical cavity SiGe quantum cascade laser capable to operate in the THz region of the electromagnetic spectrum

APPROACH:

•Characterization of ISB lifetimes in p-SiGe QWs

•Demonstrate FIR emission in p-SiGe tunnel barrier structures

•Demonstrate surface emission in p-SiGe quantum cascade structures

•Demonstrate vertical cavity SiGe quantum cascade device



Solid-State Terahertz Detector Technology



OBJECTIVE:

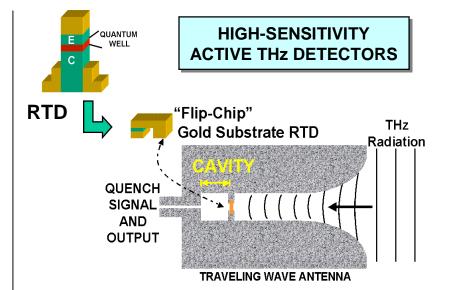
• Develop high-sensitivity, solid-state RF detector MMICs for the 0.3 - 3 THz frequency band. <u>APPROACH:</u>

•Design and develop low-parasitic InP & GaSb resonant tunneling diodes (RTDs)

•Use epitaxial transfer to integrate RTDs with low-loss THz antenna structures.

•Demonstrate passive and super-regenerative RTD detector-antenna MMICs

•Demonstrate simplex THz communication link. (with HRL & UCSB)



DOD FUTURE USES:

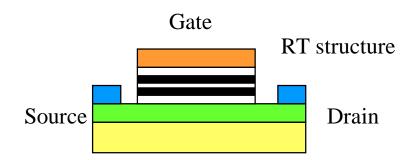
- Man-portable, ultra-secure THz communication links
- Space-based imaging of upper atmosphere
- Phased array missile seekers/munitions



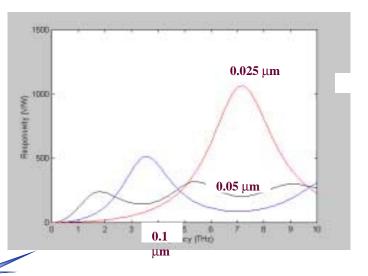


Plasma Wave Terahertz Electronics





Enhanced detectivity in sub-micron HEMT structures



OBJECTIVES:

- •Demonstrate resonant terahertz detector with high sensitivity
- •Observe terahertz radiation from a field effect transistor
- •Explore applications of plasma wave electronics to silicon

APPROACH:

- •Implement detectors using GaN based HEMTs
- •Increase the growth of plasma waves using resonant tunneling structure
- •Use "light" electrons in deep submicron silicon



THz Molecular Interactions



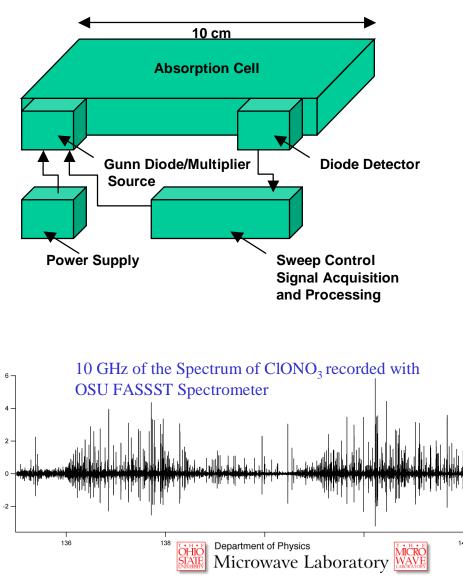
OBJECTIVE:

Build test bed for compact THz sources and detectors.

Experimentally determine rotational energy level spectrum of various gas phase molecules

TECHNICAL CHALLENGES:

- •Specific identification of chemical species
- •Quick response (< 1 second)
- •Small (<< 1 ft3)
- •Low Power
- •Simple-Based on FASSST Concept •Potentially Inexpensive in Quantity



FASSST Point-Sensor Test Bed

THz Detection Based on Photon-assisted Tunneling on Double Quantum Wells

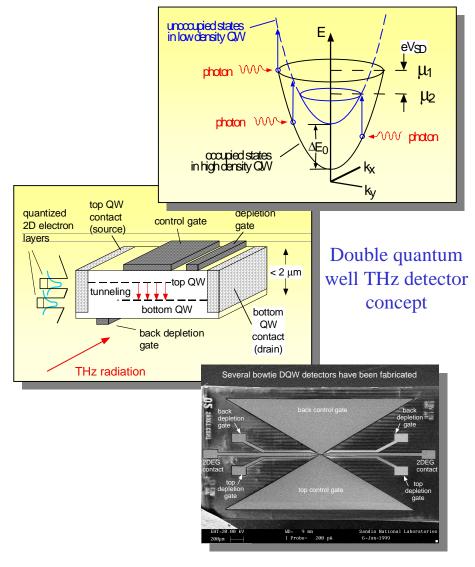


OBJECTIVE:

Demonstrate tunable, narrowband photon-assisted tunneling in double quantum well (DQW) heterostructures.

TECHNICAL APPROACH:

- Use bandgap engineering to optimize photodetector performance.
- Develop antenna structure compatible with THz detectors
- Bench-demonstration of THz detector system

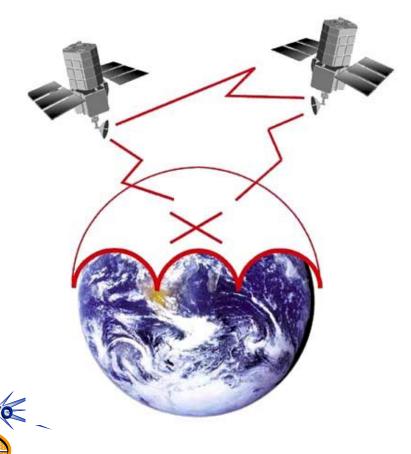




Summary



DARPA is Creating Future Opportunities for THz Technology in:



- Environmental sensing
- Upper-atmosphere imagery
- Covert satellite communications
- Chem/Bio Detection (Near Distance)